

### 1N5807-1N5811

### HIGH EFFICIENCY RECTIFIERS

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Working peak reverse voltage			
1N5807		50	
1N5808	$V_{\scriptscriptstyle RWM}$	75	V
1N5809	<b>V</b> RWM	100	V
1N5810		125	
1N5811		150	
Forward surge current (1)	I <sub>FSM</sub>	125	Α
Average rectified output current @ T <sub>L</sub> = 75°C at 3/8" lead length (2)	I <sub>01</sub>	6.0	Α
Average rectified output current @ T <sub>A</sub> = 55°C at 3/8" lead length (3)	I <sub>O2</sub>	3.0	Α
Capacitance @ $V_R = 10V$ , $f = 1MHz$ , $V_{sig} = 50mV(p-p)$	С	60	pF
Reverse recovery time <sup>(4)</sup>	t <sub>rr</sub>	30	ns
Solder temperature @ 10 s	T <sub>SP</sub>	260	°C
Junction and storage temperature range	$T_J$ , $T_{stg}$	-65 to +175	°C
Thermal resistance junction to lead (L = 0.375")	$R_{\Theta JL}$	22	°C/W

Note 1:  $T_A = 25$ °C @  $I_O = 3.0$ A and  $V_{RWM}$  for 10 8.3ms surges at 1 minute intervals.

Note 2:  $I_{01}$  is rated @  $T_L$  = 75°C at 3/8" lead length. Derate at 60mA/°C for  $T_L$  above 75°C.

Note 3:  $_{02}$  is derated at 25mA/\*C above TA = 55°C for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled where  $T_{J(max)}$  175°C is not exceeded.

Note 4:  $I_F = 1.0A$ ,  $I_{RM} = 1.0A$ ,  $I_{R(REC)} = 0.10A$ . and  $di/dt = 100A/\mu s$  min.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Part	Minimum breakdown voltage @ 100μA	Maximum forward voltage @ 4A (8.3ms pulse)		Maximum reverse current @ V <sub>RWM</sub>		Maximum surge current <sup>(5)</sup>	Maximum reverse recovery time <sup>(6)</sup>
number	V <sub>(BR)</sub>	$V_{FM}$		I <sub>R</sub>		I <sub>FSM</sub>	t <sub>rr</sub>
	Volts	Volts		μΑ		Amns	ne
		25°C	125°C	25°C	125°C	Amps	ns
1N5807	60	0.875	0.800	5	525	125	30
1N5808	85	0.875	0.800	5	525	125	30
1N5809	110	0.875	0.800	5	525	125	30
1N5810	135	0.875	0.800	5	525	125	30
1N5811	160	0.875	0.800	5	525	125	30

Note 5:  $T_A$  = 25°C @  $I_O$  = 3.0A and  $V_{RWM}$  for ten 8.3ms surges at 1 minute intervals.

Note 6:  $I_F$  = 1.0A,  $I_{RM}$  = 1.0A,  $I_{R(REC)}$  = 0.10A and di/dt = 100A/ $\mu$ s min.

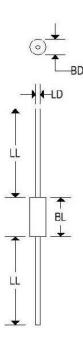


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#### MECHANICAL CHARACTERISTICS

Case	Digi B
Marking	Alpha Numeric
Polarity	Cathode Band



	DIGI B					
	Inc	hes	Millimeters			
	Min	Max	Min	Max		
BD	Ε.	0.145		3.680		
BL	201	0.300	120	7.620		
LD	0.037	0.043	0.940	1.092		
LL	0.975	- 190	24.800	Α.,		



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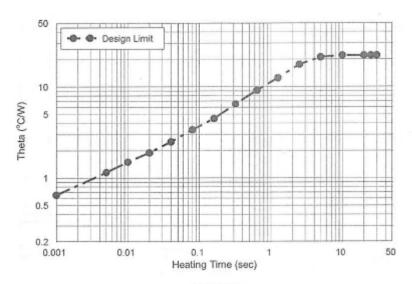


FIGURE 1 Maximum Thermal Impedance

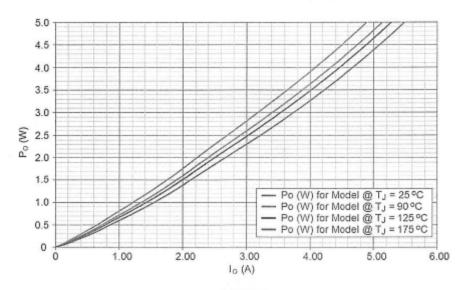


FIGURE 2

Rectifier Power vs Io (Average Forward Current)



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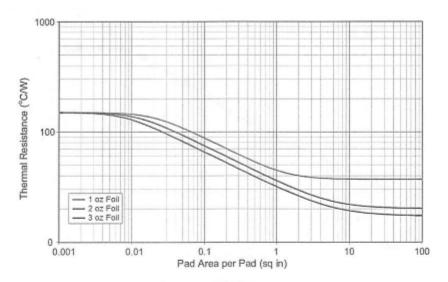


FIGURE 3
Thermal Resistance vs FR4 Pad Area At Ambient
PCB horizontal (for each pad) with 1, 2, and 3 oz copper

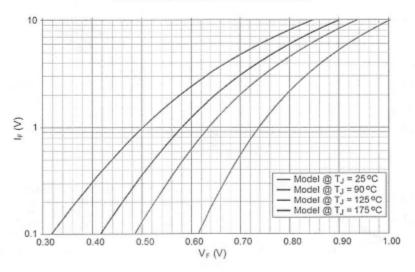


FIGURE 4
Forward Voltage vs Forward Current